

Problems

1. What are the advantages and disadvantages in the wet etching process using Silicon?
2. If a wafer goes through an ideal isotropic wet etching process with an etching rate of $1.6 \mu\text{m}/\text{min}$ for 22 seconds, what will the vertical depth of the etch be in the silicon wafer? What will be the width of the etch?
3. Design a mask for a $15\mu\text{m}$ -long, $5\mu\text{m}$ -deep v-groove trench using EDP (anisotropic). How wide should the mask window be? If EDP has a Si $\langle 100 \rangle$ -plane-etch-rate of $1\mu\text{m}/\text{min}$, how long should the etchant be applied?
4. Give an example of two different kinds of etch stops and describe how they work.